

Amendments to the Claims:

The following listing of claims will replace all prior versions, and listings, of claims in the application:

1-15. (Cancelled)

16. (Currently Amended) An active matrix substrate comprising:

a substrate;

a backing insulating layer on the substrate;

~~a source portion formed over the substrate; backing insulating layer;~~

~~a drain portion formed over the substrate; backing insulating layer;~~

a first insulating film formed over the ~~substrate, backing insulating layer,~~ the first insulating film separating the source portion and the drain portion;

a semiconductor layer formed on at least a part of the source portion, at least a part of the drain portion, and at least a part of the first insulating film;

a gate insulating layer formed over the semiconductor layer; and

a gate electrode formed over the gate insulating layer.

17. (Previously Presented) The active matrix substrate according to claim 16,

further comprising a second insulating film formed around the semiconductor layer, the second insulating film not being formed over the semiconductor layer.

18. (Previously Presented) The active matrix substrate according to claim 16, further comprising a source electrode contacting the source portion via a first contact hole, the first contact hole being formed at least in the gate insulating layer.

19. (Previously Presented) The active matrix substrate according to claim 16, further comprising a drain electrode contacting the drain portion via a second contact hole, the second contact hole being formed at least in the gate insulating layer.

20. (Previously Presented) The active matrix substrate according to claim 16, wherein a thickness of the first insulating film is larger than a thickness of the source portion.

21. (Previously Presented) The active matrix substrate according to claim 16, wherein the first insulating film is a separation wall surrounding the source portion.

22. (Previously Presented) The active matrix substrate according to claim 16, wherein the first insulating film includes a silicon oxide.

23. (Previously Presented) The active matrix substrate according to claim 16, wherein a thickness of a first part of the semiconductor layer on the source portion is different from a thickness of a second part of the semiconductor layer on the first insulating film.

24. (Previously Presented) The active matrix substrate according to claim 16, wherein a thickness of a first part of the semiconductor layer on the source portion is thinner than a thickness of a second part of the semiconductor layer on the first insulating film.

25. (Previously Presented) The active matrix substrate according to claim 16, wherein the gate electrode overlaps at least a part of the source portion.

26. (Previously Presented) An electro-optic device having the active matrix substrate according to claim 16.

27. (Previously Presented) An electronic instrument having the electro-optic device according to claim 26.

28. (New) An active matrix substrate comprising:
an insulating substrate;
a source portion formed over the insulating substrate;
a drain portion formed over the insulating substrate;
a first insulating film formed over the insulating substrate, the first insulating film separating the source portion and the drain portion;

a semiconductor layer formed on at least a part of the source portion, at least a part of the drain portion, and at least a part of the first insulating film;

a gate insulating layer formed over the semiconductor layer; and

a gate electrode formed over the gate insulating layer.

29. (New) The active matrix substrate according to claim 16, further comprising:

a backing insulating layer on the insulating substrate, wherein the source portion, the drain portion and the first insulating film are formed on the backing insulating layer.

30. (New) The active matrix substrate according to claim 28, further comprising a second insulating film formed around the semiconductor layer, the second insulating film not being formed over the semiconductor layer.

31. (New) The active matrix substrate according to claim 28, further comprising a source electrode contacting the source portion via a first contact hole, the first contact hole being formed at least in the gate insulating layer.

32. (New) The active matrix substrate according to claim 28, further comprising a drain electrode contacting the drain portion via a second contact hole, the second contact hole being formed at least in the gate insulating layer.

33. (New) The active matrix substrate according to claim 28, wherein a thickness of the first insulating film is larger than a thickness of the source portion.

34. (New) The active matrix substrate according to claim 28, wherein the first insulating film is a separation wall surrounding the source portion.

35. (New) The active matrix substrate according to claim 28, wherein the first insulating film includes a silicon oxide.

36. (New) The active matrix substrate according to claim 28, wherein a thickness of a first part of the semiconductor layer on the source portion is different from a thickness of a second part of the semiconductor layer on the first insulating film.

37. (New) The active matrix substrate according to claim 28, wherein a thickness of a first part of the semiconductor layer on the source portion is thinner than a thickness of a second part of the semiconductor layer on the first insulating film.

38. (New) The active matrix substrate according to claim 28, wherein the gate electrode overlaps at least a part of the source portion.

39. (New) An electro-optic device having the active matrix substrate according to claim 28.

40. (New) The active matrix substrate according to claim 28, further comprising:
a backing insulating layer on the insulating substrate, wherein the source portion, the drain portion and the first insulating film are formed on the backing insulating layer.